Three quadrant triacs high commutation

BTA225 series C

GENERAL DESCRIPTION

Glass passivated high commutation triacs in a plastic envelope intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur loads. These devices will commutate the full rated rms current at the maximum rated junction temperature, without the aid of a snubber.

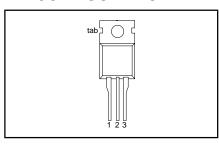
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V _{DRM} I _{T(RMS)} I _{TSM}	BTA225- Repetitive peak off-state voltages RMS on-state current Non-repetitive peak on-state current	500C 500 25 190	600C 600 25 190	800C 800 25 190	V A A

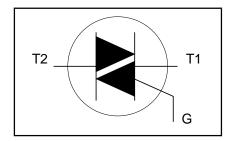
PINNING - TO220AB

PIN	N DESCRIPTION		
1	main terminal 1		
2	main terminal 2		
3	gate		
tab	main terminal 2		

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT	
				-500	-600	-800	
V_{DRM}	Repetitive peak off-state voltages		-	600 ¹	600 ¹	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave;	-		25		A
I _{TSM}	Non-repetitive peak on-state current	$T_{mb} \le 91$ °C full sine wave; $T_{j} = 25$ °C prior to surge t = 20 ms	_		190		A
-2		t = 16.7 ms	-		209		A A ² s
l²t dl _⊤ /dt	l ² t for fusing Repetitive rate of rise of on-state current after	$I_{TM} = 30 \text{ A}; I_{G} = 0.2 \text{ A}; \\ dI_{G}/dt = 0.2 \text{ A}/\mu\text{s}$	-	180 100		A²s A/μs	
${ m I}_{ m GM} \ { m V}_{ m GM}$	triggering Peak gate current Peak gate voltage		-		2 5 5		A V
P_{GM} $P_{G(AV)}$	Peak gate power Average gate power	over any 20 ms	-		5 0.5		W
T_{stg}	Storage temperature Operating junction temperature	репои	-40 -	150 125		°C	

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¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 $A/\mu s$.

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THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th j-mb}$ $R_{th j-a}$	Thermal resistance junction to mounting base Thermal resistance junction to ambient	full cycle half cycle in free air		- - 60	1.0 1.4 -	K/W K/W K/W

STATIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

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SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
I _{GT}	Gate trigger current ²	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$					
Gi		T2+ (G+	2	18	35	mΑ
		T2+ (G-	2	21	35	mΑ
		T2- G	3-	2	34	35	mΑ
I _L	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$					
-		T2+ (G+	-	-	20	mΑ
		T2+ (G-	-	-	30	mΑ
		T2- G	3-	-	-	20	mΑ
l I _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$		-	-	15	mΑ
V _T	On-state voltage	$I_{T} = 30 \text{ A}$		-	1.3	1.55	V
V _{GT}	Gate trigger voltage	$\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$		-	0.7	1.5	V
	1	$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_L = 125 \text{ °C}$		0.25	0.4	-	V
I_{D}	Off-state leakage current	$V_D = V_{DRM(max)}$; $T_j = 125 °C$		-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

 $T_j = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125 °C;$	1000	-	-	V/μs
dl _{com} /dt	off-state voltage Critical rate of change of	exponential waveform; gate open circuit $V_{DM} = 400 \text{ V}$; $T_j = 125 \text{ °C}$; $I_{T(RMS)} = 25 \text{ A}$;	-	14	-	A/ms
t _{gt}	commutating current Gate controlled turn-on time	without snubber; gate open circuit $I_{TM} = 30 \text{ A}$; $V_D = V_{DRM(max)}$; $I_G = 0.1 \text{ A}$; $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

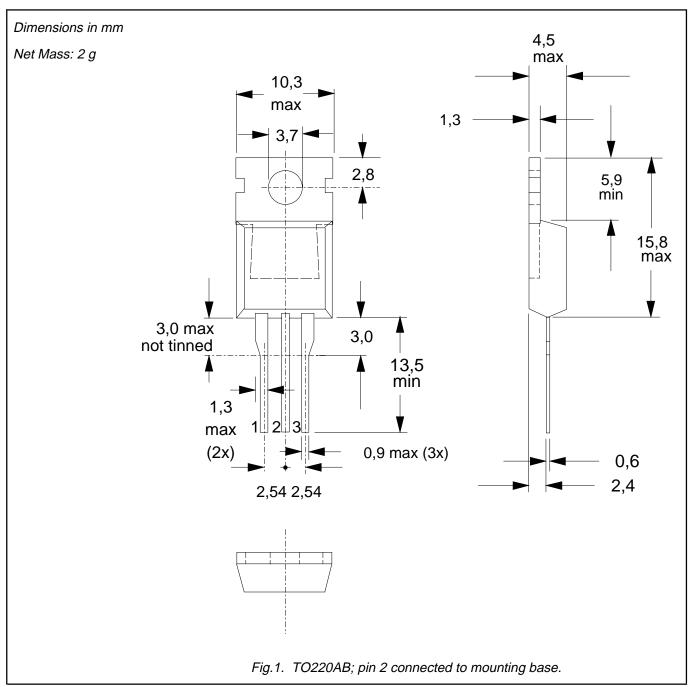
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² Device does not trigger in the T2-, G+ quadrant.

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MECHANICAL DATA



- Refer to mounting instructions for TO220 envelopes.
 Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status					
Objective specification	This data sheet contains target or goal specifications for product development.				
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.				
Product specification	This data sheet contains final product specifications.				

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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